

IN THE CLAIMS:

Please cancel Claims 1 to 16 without prejudice to or disclaimer of the subject matter presented therein. Please amend Claims 17 to 19, 22, 23, and 26 as shown below.

1 to 16. (Cancelled)

17. (Currently Amended) ~~The method according to claim 1, further comprising~~ A method of manufacturing a semiconductor film separated from a seed substrate, comprising:

~~a step of forming, between the seed substrate and the separation layer;~~ a separation assisting layer on the seed substrate;

a separation layer forming step of hetero-epitaxially growing a separation layer on the separation assisting layer;

a semiconductor film forming step of forming a semiconductor film on the separation layer; and

a separation step of separating, by using the separation layer, the semiconductor film from a composite member formed in the semiconductor film forming step.

wherein the separation assisting layer is formed by using a material to be selectively etched with respect to the substrate and the separation layer.

18. (Currently Amended) ~~The method according to claim 1, further comprising~~ A method of manufacturing a semiconductor film separated from a seed substrate, comprising:

~~a step of forming a separation assisting layer between the seed substrate and the separation layer; on the seed substrate;~~

a separation layer forming step of hetero-epitaxially growing a separation layer on the separation assisting layer;

a semiconductor film forming step of forming a semiconductor film on the separation layer; and

a separation step of separating, by using the separation layer, the semiconductor film from a composite member formed in the semiconductor film forming step,

wherein the separation assisting layer containing contains Al in a larger amount than layers in contact with the separation assisting layer.

19. (Currently Amended) ~~The method according to claim 1, further comprising~~ A method of manufacturing a semiconductor film separated from a seed substrate, comprising:

~~a step of forming a separation assisting layer between the seed substrate and the separation layer; on the seed substrate;~~

a separation layer forming step of hetero-epitaxially growing a separation layer on the separation assisting layer;

a semiconductor film forming step of forming a semiconductor film on the

separation layer; and

a separation step of separating, by using the separation layer, the semiconductor film from a composite member formed in the semiconductor film forming step,

wherein the separation assisting layer being is made of a material which satisfies Al_xGa_{1-x}As (x > 0.95).

20. (Original) The method according to claim 17, further comprising, before the separation step, a step of etching a periphery of the separation assisting layer.

21. (Original) The method according to claim 20, wherein in the separation step, a fluid is blown to or near the separation layer on a side surface of the composite member.

22. (Currently Amended) ~~The method according to claim 1, further comprising, after the semiconductor film forming step before the separation step, A method of manufacturing a semiconductor film separated from a seed substrate, comprising:~~
a separation layer forming step of hetero-epitaxially growing a separation layer on the seed substrate;

a semiconductor film forming step of forming a semiconductor film on the separation layer;

a bonding step of bonding the seed substrate ~~with~~ on which the separation layer and the semiconductor film have been formed, to a handle substrate while setting the

separation layer inside[[],]; and

~~wherein in the separation step, the semiconductor film is separated; a separation step of separating the semiconductor film together with the handle substrate substrate, by using the separation layer, from the a composite member formed in the bonding step.~~

23. (Currently Amended) The method according to claim 1, further comprising A method of manufacturing a semiconductor film separated from a seed substrate, comprising:

a separation layer forming step of hetero-epitaxially growing a separation layer on the seed substrate;

a semiconductor film forming step of forming a semiconductor film on the separation layer;

a separation step of separating, by using the separation layer, the semiconductor film from a composite member formed in the semiconductor film forming step; and

a device forming step of forming a semiconductor device on the semiconductor film.

24. (Original) The method according to claim 23, wherein the device forming step is executed before the bonding step.

25. (Original) The method according to claim 23, wherein the device

forming step is executed after the separation step.

26. (Currently Amended) ~~The method according to claim 1, A method of manufacturing a semiconductor film separated from a seed substrate, comprising:~~

a separation layer forming step of hetero-epitaxially growing a separation layer on the seed substrate;

a semiconductor film forming step of forming a semiconductor film on the separation layer; and

a separation step of separating, by using the separation layer, the semiconductor film from a composite member formed in the semiconductor film forming step,

wherein another semiconductor film is manufactured by further executing the separation layer forming step and subsequent steps by using the seed substrate remaining after the separation step as a raw material.

27. (Original) A method of manufacturing a substrate having a semiconductor film, comprising:

a separation layer forming step of hetero-epitaxially growing a separation layer on a seed substrate;

a semiconductor film forming step of forming a semiconductor film on the separation layer;

a bonding step of bonding the seed substrate with the separation layer and the semiconductor film to a handle substrate while setting the separation layer inside; and

a separation step of separating the semiconductor film, together with the handle substrate by using the separation layer, from a composite member formed in the bonding step to obtain a substrate having the semiconductor film on the handle substrate.

28. (Original) The method according to claim 27, further comprising a device forming step of forming a semiconductor device in the semiconductor film.

29. (Original) The method according to claim 28, wherein the device forming step is executed before the bonding step.

30. (Original) The method according to claim 28, wherein the device forming step is executed after the separation step.

31. (Original) The method according to claim 28, wherein the semiconductor device includes one of a light-emitting diode and a laser.